TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2998

#### Chopper Regulator, DC-DC Converter Applications

Unit: mm

| • | Low drain-source ON resis | tance          | $: RDS (ON) = 11.5 \Omega (typ.)$                                    |
|---|---------------------------|----------------|--|
| • | High forward transfer adm | ittance        | $ Y_{fs}  = 0.4 \text{ S (typ.)}$                                    |
| • | Low leakage current       | $I_{DSS} = 10$ | $100 \mu\text{A} (\text{max}) (\text{V}_{\text{DS}} = 500 \text{V})$ |
| • | Enhancement mode          | $V_{th} = 2.0$ | $0\sim4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$   |
|   |                           |                |  |

#### Absolute Maximum Ratings (Ta = 25°C)

| Characteristics         |                        | Symbol           | Rating  | Unit |  |
|-------------------------|------------------------|------------------|---------|------|--|
| Drain-source voltage    |                        | $V_{DSS}$        | 500     | V    |  |
| Drain-gate voltage (Ro  | <sub>SS</sub> = 20 kΩ) | $V_{DGR}$        | 500     | V    |  |
| Gate-source voltage     |                        | $V_{GSS}$        | ±30     | V    |  |
| Drain current           | DC (Note 1)            | I <sub>D</sub>   | 0.5     | Α    |  |
| Dialii cuitent          | Pulse (Note 1)         | I <sub>DP</sub>  | 1.5     | Α    |  |
| Drain power dissipation | ١                      | $P_{D}$          | 0.9     | W    |  |
| Channel temperature     |                        | T <sub>ch</sub>  | 150     | °C   |  |
| Storage temperature ra  | ange                   | T <sub>stg</sub> | -55~150 | °C   |  |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

# 5.1 max 0.75 max 1.0 max 10.5 min 0.8 max 0.6 max 1.27 1.27 2.54 l max 1 2 3 1.SOURCE 2.DRAIN 3.GATE **JEDEC** TO-92MOD JEITA TOSHIBA 2-5J1C

Weight: 0.36 g (typ.)

#### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max | Unit |
|--|------------------------|-----|------|
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 138 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

This transistor is an electrostatic-sensitive device.

Please handle with caution.



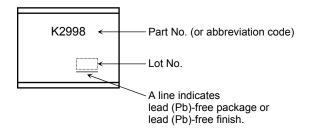
## **Electrical Characteristics (Ta = 25°C)**

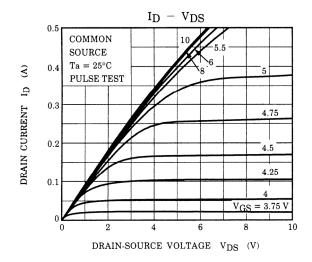
| Charac  | eteristics    | Symbol               | Test Condition   |     | Тур. | Max | Unit |
|---|---------------|----------------------|--|-----|------|-----|------|
| Gate leakage current                            |               | I <sub>GSS</sub>     | V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V   |     | _    | ±10 | μA   |
| Gate-source breakdown voltage                   |               | V (BR) GSS           | I <sub>D</sub> = ±10 mA, V <sub>GS</sub> = 0 V   |     | _    | _   | V    |
| Drain cut-off current                           |               | I <sub>DSS</sub>     | V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V   | _   | _    | 100 | μA   |
| Drain-source breakdown voltage                  |               | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V  | 500 | _    | _   | V    |
| Gate threshold v                                | roltage       | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA  | 2.0 | _    | 4.0 | V    |
| Drain-source ON resistance                      |               | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.25 A  | _   | 11.5 | 18  | Ω    |
| Forward transfer                                | admittance    | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.25 A  | 0.2 | 0.4  | _   | S    |
| Input capacitance                               |               | C <sub>iss</sub>     |  | _   | 75   | _   |      |
| Reverse transfer capacitance                    |               | C <sub>rss</sub>     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                     | _   | 7    | _   | pF   |
| Output capacitance                              |               | C <sub>oss</sub>     |  |     | 25   | _   |      |
|   | Rise time     | t <sub>r</sub>       | $V_{GS}$ $V_{OV}$ $V_{OUT}$ $V_{OUT}$ $V_{OUT}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ $V_{DD}$ | _   | 11   | _   |      |
| Switching time                                  | Turn-on time  | t <sub>on</sub>      |  | ı   | 18   |     | ns   |
| Switching time                                  | Fall time     | t <sub>f</sub>       |  | ı   | 54   |     |      |
|   | Turn-off time | t <sub>off</sub>     |  |     | 95   | _   |      |
| Total gate charge (gate-source plus gate-drain) |               | Qg                   |  |     | 3.8  |     |      |
| Gate-source charge                              |               | Q <sub>gs</sub>      | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 0.5 \text{ A}$                 |     | 1.9  | _   | nC   |
| Gate-drain ("miller") charge                    |               | $Q_{gd}$             |  | _   | 1.9  | _   |      |

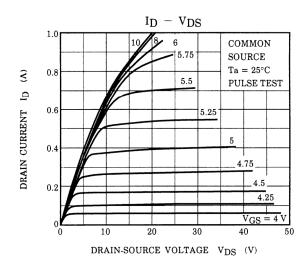
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

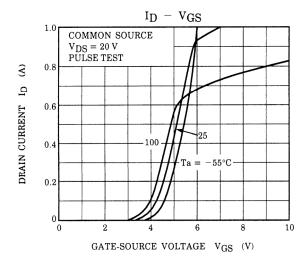
| Characteristics                           | Symbol           | Test Condition                                    | Min | Тур. | Max  | Unit |
|---|------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _   | _   | _    | 0.5  | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | -   | _   | _    | 1.5  | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 0.5 A, V <sub>GS</sub> = 0 V    | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = 0.5 A, V <sub>GS</sub> = 0 V    |     | 190  | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | $dI_{DR}$ / $dt = 100 \text{ Å}$ / $\mu \text{s}$ |     | 380  | _    | nC   |

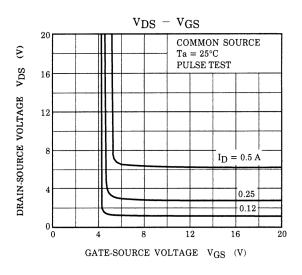
# Marking

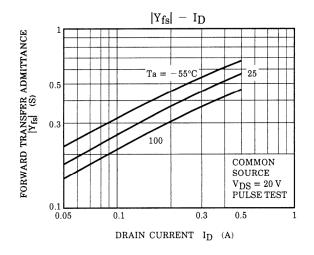


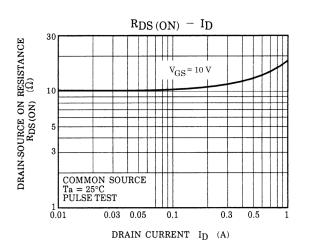




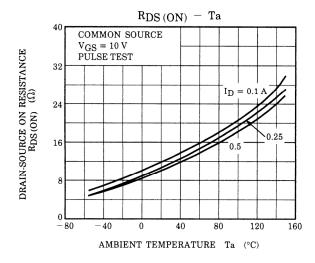


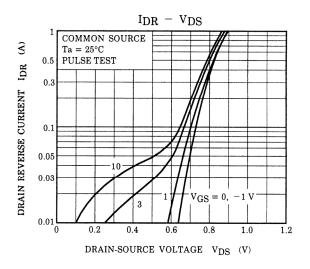


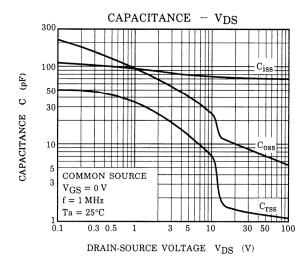


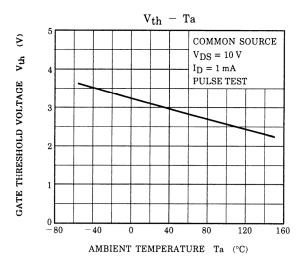


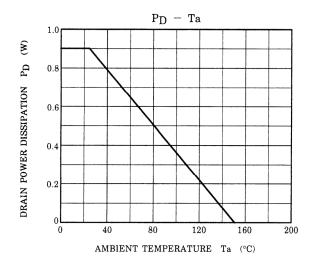
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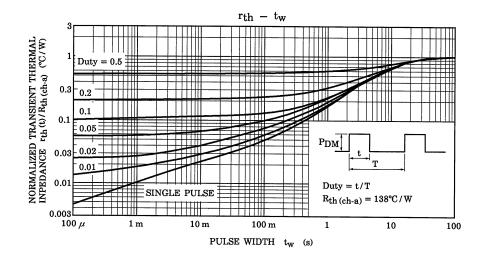


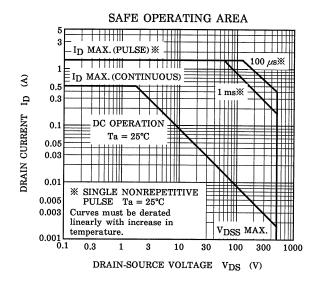












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